

isc Silicon NPN RF Transistor

2SC4308

DESCRIPTION

- Low Noise
- High Gain Bandwidth Product

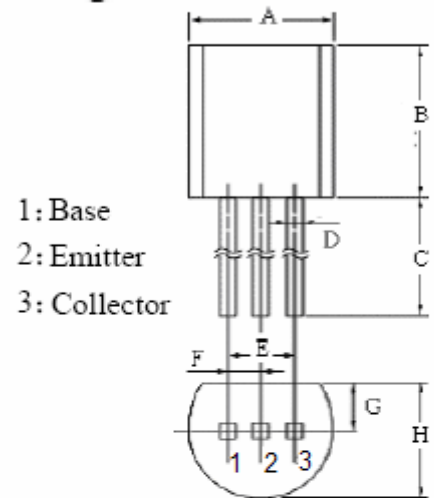
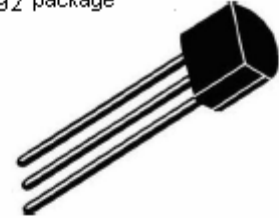
APPLICATIONS

- Designed for use in VHF wide band amplifiers.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	20	V
V _{EBO}	Emitter-Base Voltage	3	V
I _C	Collector Current-Continuous	300	mA
I _{CM}	Collector Current-Peak	500	mA
P _C	Collector Power Dissipation @T _C =25°C	0.6	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

TO-92 package



DIM	mm	
	MIN	MAX
A	4.33	4.83
B	4.33	4.83
C	14.0	15.0
D	0.36	0.56
E	2.54	
F	1.27	
G	0.92	1.12
H	3.40	3.60

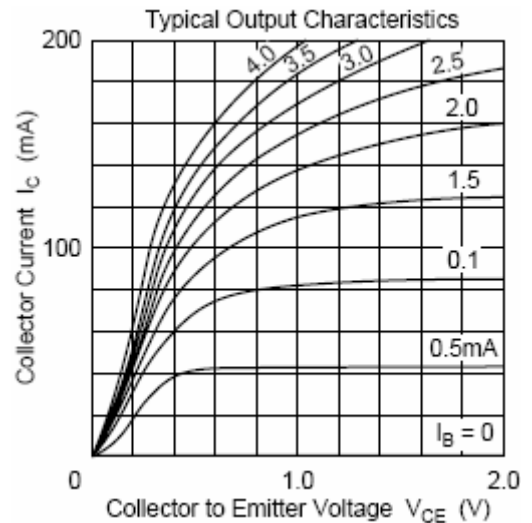
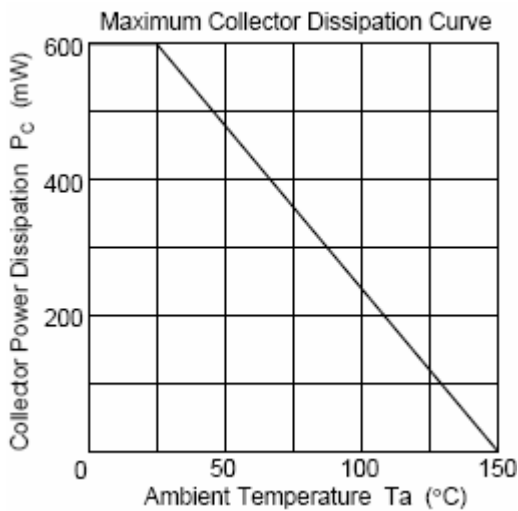
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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 100 μ A ; I _E = 0	30			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA ; R _{BE} = ∞	20			V
I _{CBO}	Collector Cutoff Current	V _{CB} = 25V; I _E = 0			1	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 3V; I _C = 0			10	μ A
h _{FE}	DC Current Gain	I _C = 50mA ; V _{CE} = 5V	50		200	
f _T	Current-Gain—Bandwidth Product	I _C = 50mA ; V _{CE} = 5V	1.5	2.5		GHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V;f= 1.0MHz		4.0		pF



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